



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China





## 600V, SMPS Series N-Channel IGBT with Anti-Parallel Hyperfast Diode

The HGTG12N60A4D, HGTP12N60A4D and HGT1S12N60A4DS are MOS gated high voltage switching devices combining the best features of MOSFETs and bipolar transistors. These devices have the high input impedance of a MOSFET and the low on-state conduction loss of a bipolar transistor. The much lower on-state voltage drop varies only moderately between 25°C and 150°C. The IGBT used is the development type TA49335. The diode used in anti-parallel is the development type TA49371.

This IGBT is ideal for many high voltage switching applications operating at high frequencies where low conduction losses are essential. This device has been optimized for high frequency switch mode power supplies.

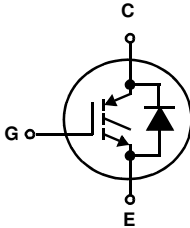
Formerly Developmental Type TA49337.

### Ordering Information

PART NUMBER	PACKAGE	BRAND
HGTG12N60A4D	TO-247	12N60A4D
HGTP12N60A4D	TO-220AB	12N60A4D
HGT1S12N60A4DS	TO-263AB	12N60A4D

NOTE: When ordering, use the entire part number. Add the suffix 9A to obtain the TO-263AB variant in tape and reel, e.g. HGT1S12N60A4DS9A.

### Symbol

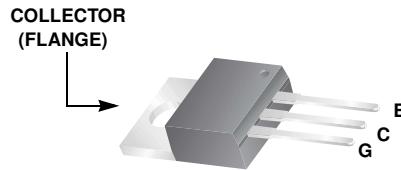


### Features

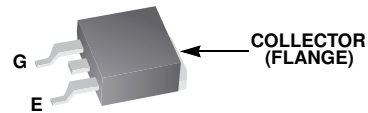
- >100kHz Operation . . . . . 390V, 12A
- 200kHz Operation . . . . . 390V, 9A
- 600V Switching SOA Capability
- Typical Fall Time. . . . . 70ns at T<sub>J</sub> = 125°C
- Low Conduction Loss
- *Temperature Compensating SABER™* Model
- Related Literature
  - TB334 "Guidelines for Soldering Surface Mount Components to PC Boards"

### Packaging

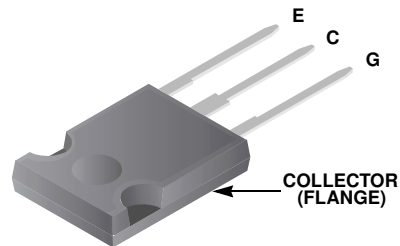
#### JEDEC TO-220AB ALTERNATE VERSION



#### JEDEC TO-263AB



#### JEDEC STYLE TO-247



# HGTG12N60A4D, HGTP12N60A4D, HGT1S12N60A4DS

## Absolute Maximum Ratings $T_C = 25^{\circ}\text{C}$ , Unless Otherwise Specified

	HGTG12N60A4D, HGTP12N60A4D, HGT1S12N60A4DS	UNITS
Collector to Emitter Voltage	600	V
Collector Current Continuous		
At $T_C = 25^{\circ}\text{C}$	54	A
At $T_C = 110^{\circ}\text{C}$	23	A
Collector Current Pulsed (Note 1)	96	A
Gate to Emitter Voltage Continuous	$\pm 20$	V
Gate to Emitter Voltage Pulsed	$\pm 30$	V
Switching Safe Operating Area at $T_J = 150^{\circ}\text{C}$ , Figure 2	60A at 600V	
Power Dissipation Total at $T_C = 25^{\circ}\text{C}$	167	W
Power Dissipation Derating $T_C > 25^{\circ}\text{C}$	1.33	W/ $^{\circ}\text{C}$
Operating and Storage Junction Temperature Range	-55 to 150	$^{\circ}\text{C}$
Maximum Temperature for Soldering		
Leads at 0.063in (1.6mm) from Case for 10s	300	$^{\circ}\text{C}$
Package Body for 10s, see Tech Brief 334	260	$^{\circ}\text{C}$

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

### NOTE:

1. Pulse width limited by maximum junction temperature.

## Electrical Specifications $T_J = 25^{\circ}\text{C}$ , Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS	
Collector to Emitter Breakdown Voltage	$BV_{CES}$	$I_C = 250\mu\text{A}$ , $V_{GE} = 0\text{V}$	600	-	-	V	
Collector to Emitter Leakage Current	$I_{CES}$	$V_{CE} = 600\text{V}$	$T_J = 25^{\circ}\text{C}$	-	-	250	$\mu\text{A}$
			$T_J = 125^{\circ}\text{C}$	-	-	2.0	mA
Collector to Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = 12\text{A}$ , $V_{GE} = 15\text{V}$	$T_J = 25^{\circ}\text{C}$	-	2.0	2.7	V
			$T_J = 125^{\circ}\text{C}$	-	1.6	2.0	V
Gate to Emitter Threshold Voltage	$V_{GE(TH)}$	$I_C = 250\mu\text{A}$ , $V_{CE} = 600\text{V}$	-	5.6	-	V	
Gate to Emitter Leakage Current	$I_{GES}$	$V_{GE} = \pm 20\text{V}$	-	-	$\pm 250$	nA	
Switching SOA	SSOA	$T_J = 150^{\circ}\text{C}$ , $R_G = 10\Omega$ , $V_{GE} = 15\text{V}$ , $L = 100\mu\text{H}$ , $V_{CE} = 600\text{V}$	60	-	-	A	
Gate to Emitter Plateau Voltage	$V_{GEP}$	$I_C = 12\text{A}$ , $V_{CE} = 300\text{V}$	-	8	-	V	
On-State Gate Charge	$Q_{g(ON)}$	$I_C = 12\text{A}$ , $V_{CE} = 300\text{V}$	$V_{GE} = 15\text{V}$	-	78	96	nC
			$V_{GE} = 20\text{V}$	-	97	120	nC
Current Turn-On Delay Time	$t_{d(ON)I}$	IGBT and Diode at $T_J = 25^{\circ}\text{C}$ , $I_{CE} = 12\text{A}$ , $V_{CE} = 390\text{V}$ , $V_{GE} = 15\text{V}$ , $R_G = 10\Omega$ , $L = 500\mu\text{H}$ , Test Circuit (Figure 24)	-	17	-	ns	
Current Rise Time	$t_{rI}$		-	8	-	ns	
Current Turn-Off Delay Time	$t_{d(OFF)I}$		-	96	-	ns	
Current Fall Time	$t_{fI}$		-	18	-	ns	
Turn-On Energy (Note 3)	$E_{ON1}$		-	55	-	$\mu\text{J}$	
Turn-On Energy (Note 3)	$E_{ON2}$		-	160	-	$\mu\text{J}$	
Turn-Off Energy (Note 2)	$E_{OFF}$		-	50	-	$\mu\text{J}$	
Current Turn-On Delay Time	$t_{d(ON)I}$		IGBT and Diode at $T_J = 125^{\circ}\text{C}$ , $I_{CE} = 12\text{A}$ , $V_{CE} = 390\text{V}$ , $V_{GE} = 15\text{V}$ , $R_G = 10\Omega$ , $L = 500\mu\text{H}$ , Test Circuit (Figure 24)	-	17	-	ns
Current Rise Time	$t_{rI}$			-	16	-	ns
Current Turn-Off Delay Time	$t_{d(OFF)I}$	-		110	170	ns	
Current Fall Time	$t_{fI}$	-		70	95	ns	
Turn-On Energy (Note3)	$E_{ON1}$	-		55	-	$\mu\text{J}$	
Turn-On Energy (Note 3)	$E_{ON2}$	-		250	350	$\mu\text{J}$	
Turn-Off Energy (Note 2)	$E_{OFF}$	-		175	285	$\mu\text{J}$	

# HGTG12N60A4D, HGTP12N60A4D, HGT1S12N60A4DS

## Electrical Specifications $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Diode Forward Voltage	$V_{EC}$	$I_{EC} = 12\text{A}$	-	2.2	-	V
Diode Reverse Recovery Time	$t_{rr}$	$I_{EC} = 12\text{A}, dI_{EC}/dt = 200\text{A}/\mu\text{s}$	-	30	-	ns
		$I_{EC} = 1\text{A}, dI_{EC}/dt = 200\text{A}/\mu\text{s}$	-	18	-	ns
Thermal Resistance Junction To Case	$R_{\theta JC}$	IGBT	-	-	0.75	$^\circ\text{C}/\text{W}$
		Diode	-	-	2.0	$^\circ\text{C}/\text{W}$

### NOTES:

- Turn-Off Energy Loss ( $E_{OFF}$ ) is defined as the integral of the instantaneous power loss starting at the trailing edge of the input pulse and ending at the point where the collector current equals zero ( $I_{CE} = 0\text{A}$ ). All devices were tested per JEDEC Standard No. 24-1 Method for Measurement of Power Device Turn-Off Switching Loss. This test method produces the true total Turn-Off Energy Loss.
- Values for two Turn-On loss conditions are shown for the convenience of the circuit designer.  $E_{ON1}$  is the turn-on loss of the IGBT only.  $E_{ON2}$  is the turn-on loss when a typical diode is used in the test circuit and the diode is at the same  $T_J$  as the IGBT. The diode type is specified in Figure 24.

## Typical Performance Curves Unless Otherwise Specified

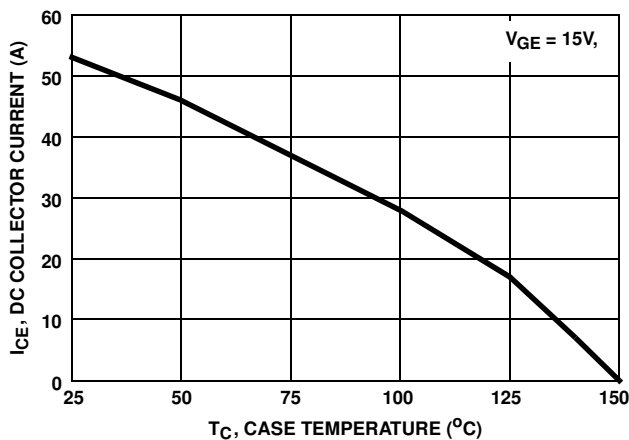


FIGURE 1. DC COLLECTOR CURRENT vs CASE TEMPERATURE

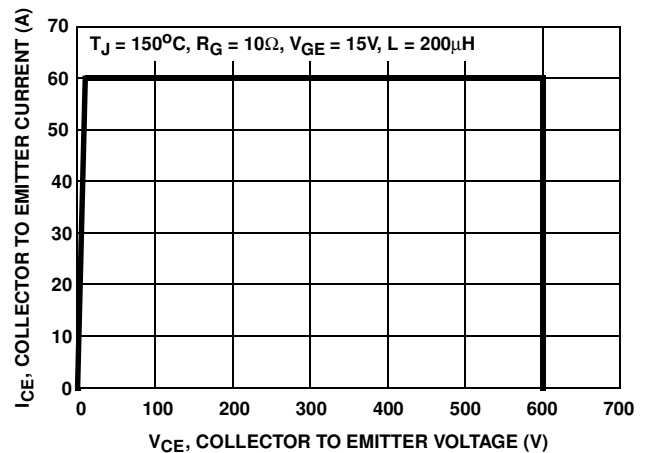


FIGURE 2. MINIMUM SWITCHING SAFE OPERATING AREA

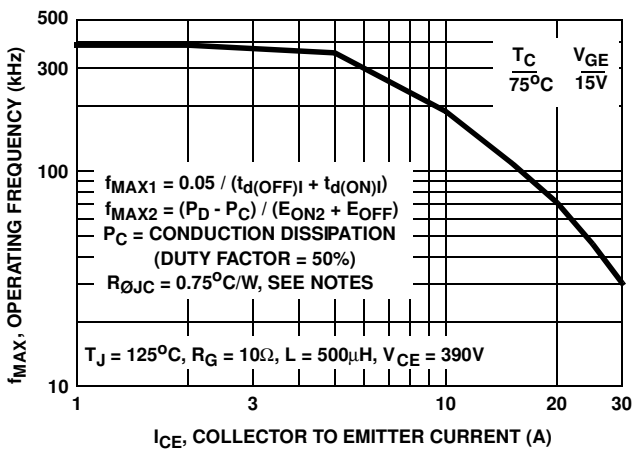


FIGURE 3. OPERATING FREQUENCY vs COLLECTOR TO EMITTER CURRENT

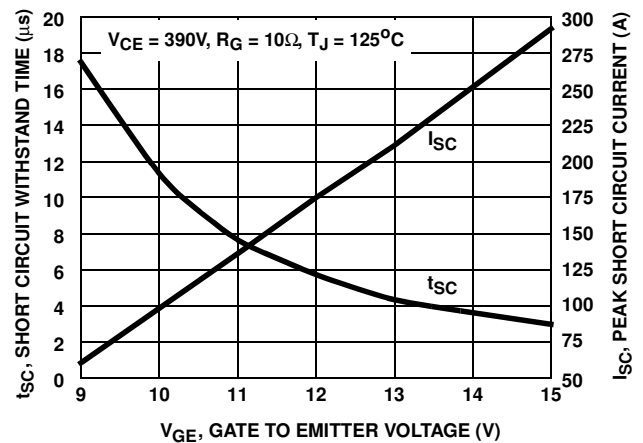


FIGURE 4. SHORT CIRCUIT WITHSTAND TIME

Typical Performance Curves Unless Otherwise Specified (Continued)

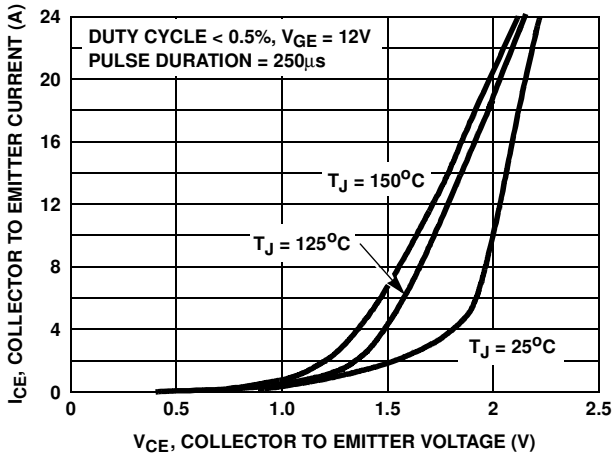


FIGURE 5. COLLECTOR TO EMITTER ON-STATE VOLTAGE

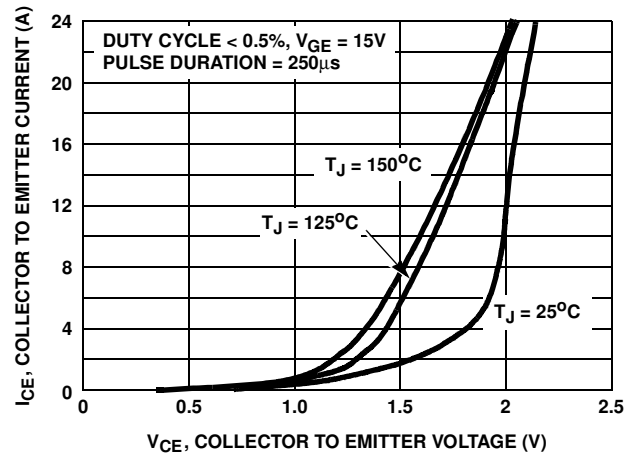


FIGURE 6. COLLECTOR TO EMITTER ON-STATE VOLTAGE

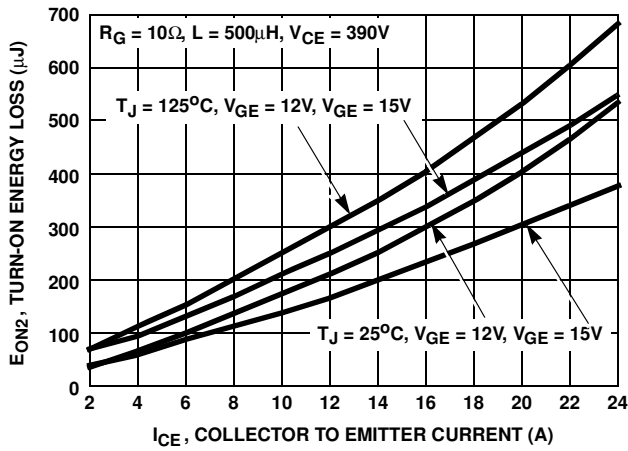


FIGURE 7. TURN-ON ENERGY LOSS vs COLLECTOR TO EMITTER CURRENT

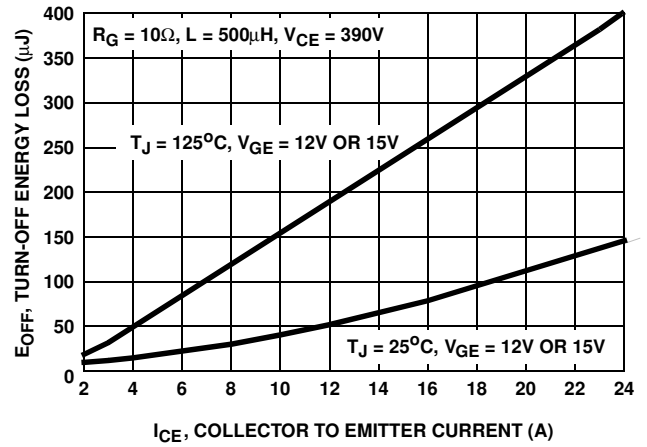


FIGURE 8. TURN-OFF ENERGY LOSS vs COLLECTOR TO EMITTER CURRENT

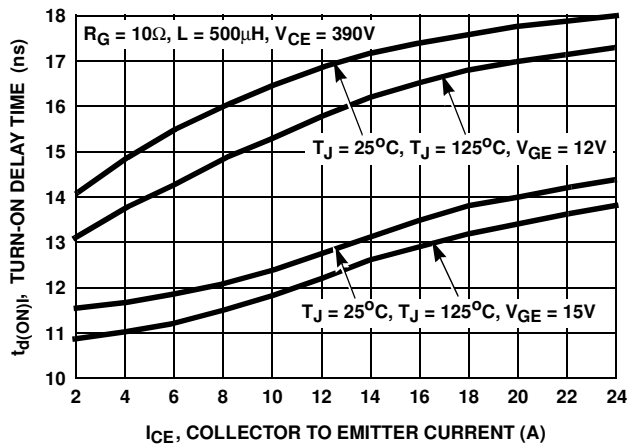


FIGURE 9. TURN-ON DELAY TIME vs COLLECTOR TO EMITTER CURRENT

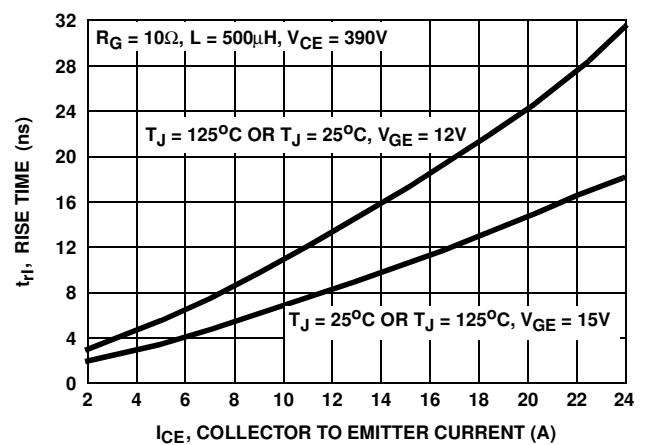


FIGURE 10. TURN-ON RISE TIME vs COLLECTOR TO EMITTER CURRENT



Typical Performance Curves Unless Otherwise Specified (Continued)

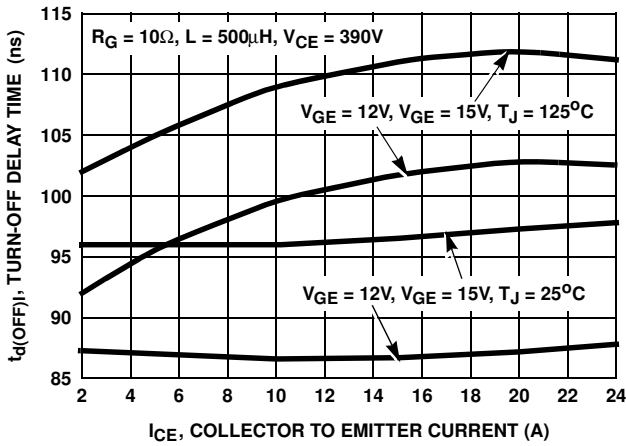


FIGURE 11. TURN-OFF DELAY TIME vs COLLECTOR TO EMITTER CURRENT

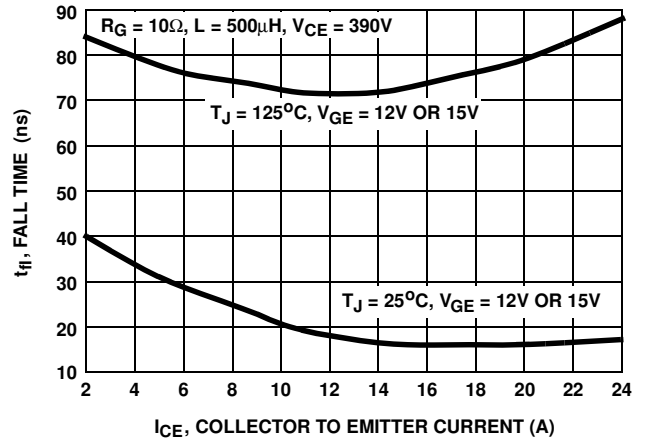


FIGURE 12. FALL TIME vs COLLECTOR TO EMITTER CURRENT

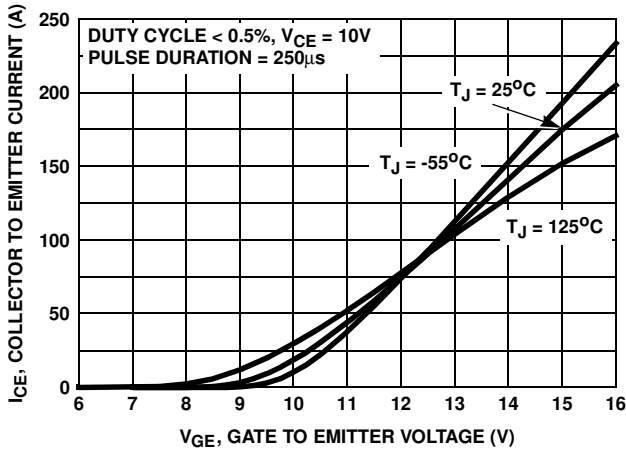


FIGURE 13. TRANSFER CHARACTERISTIC

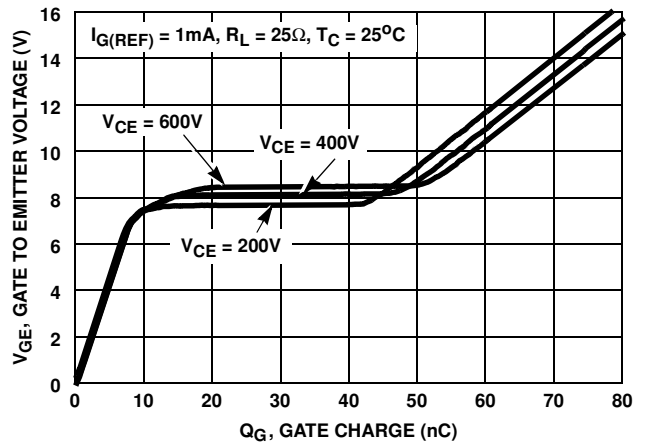


FIGURE 14. GATE CHARGE WAVEFORMS

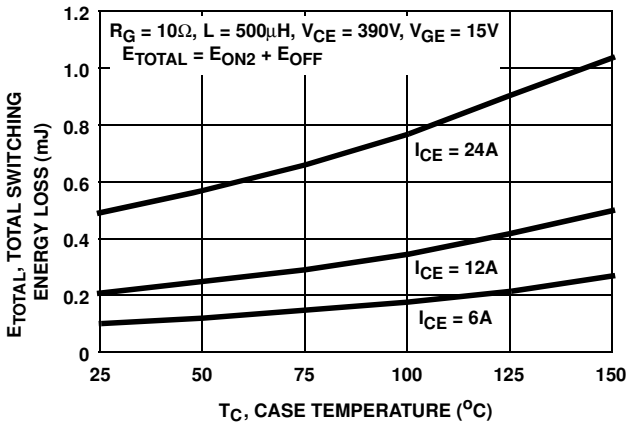


FIGURE 15. TOTAL SWITCHING LOSS vs CASE TEMPERATURE

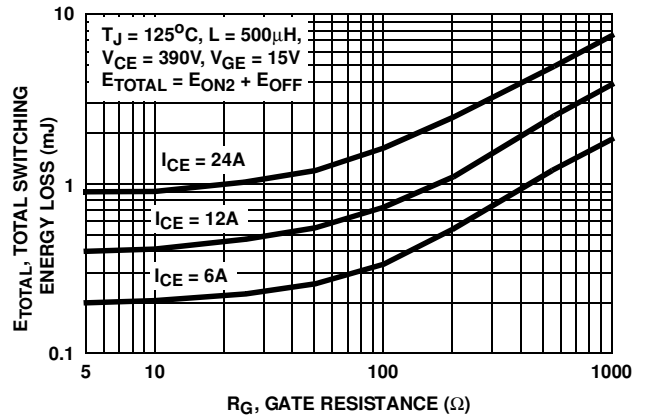


FIGURE 16. TOTAL SWITCHING LOSS vs GATE RESISTANCE

Typical Performance Curves Unless Otherwise Specified (Continued)

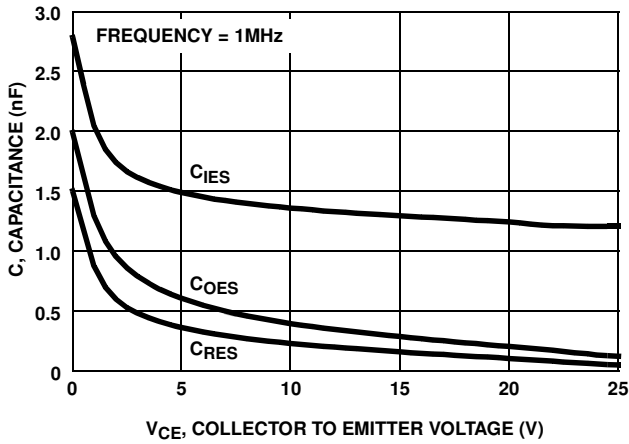


FIGURE 17. CAPACITANCE vs COLLECTOR TO EMITTER VOLTAGE

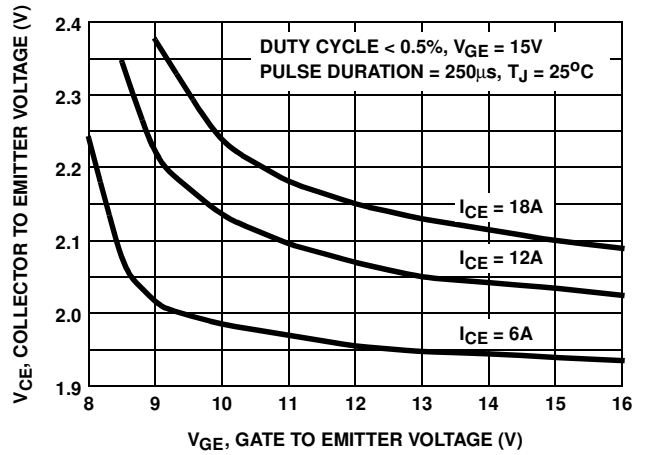


FIGURE 18. COLLECTOR TO EMITTER ON-STATE VOLTAGE vs GATE TO EMITTER VOLTAGE

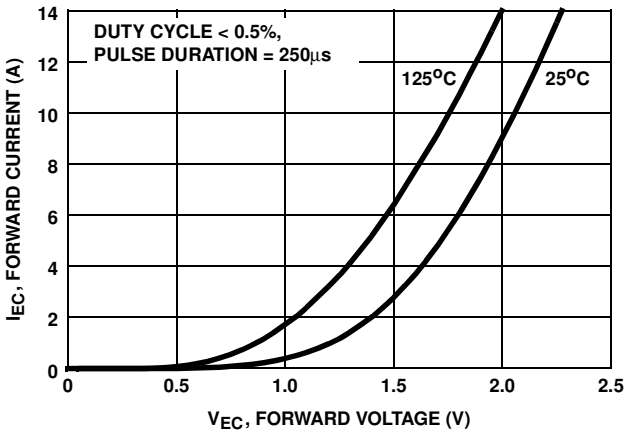


FIGURE 19. DIODE FORWARD CURRENT vs FORWARD VOLTAGE DROP

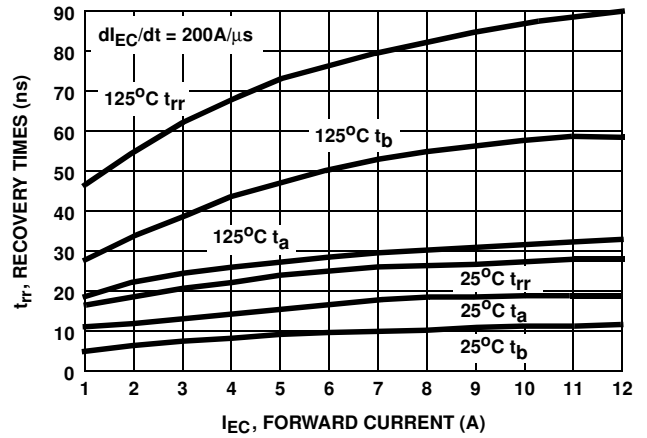


FIGURE 20. RECOVERY TIMES vs FORWARD CURRENT

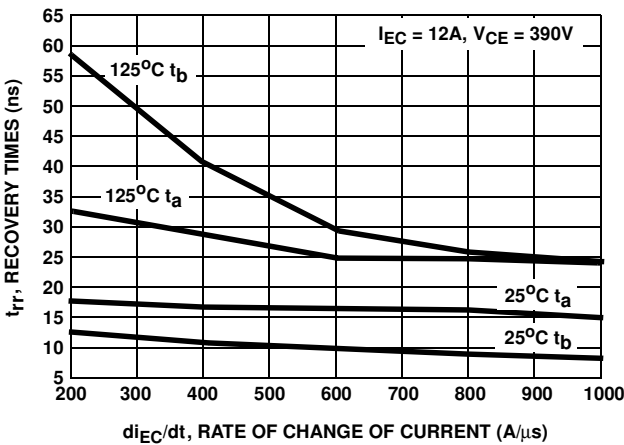


FIGURE 21. RECOVERY TIMES vs RATE OF CHANGE OF CURRENT

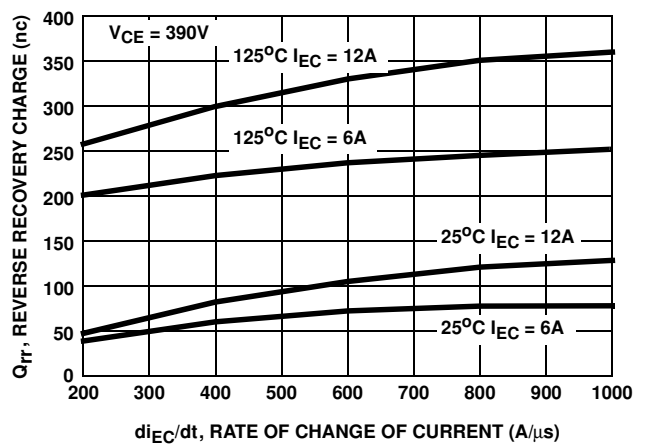


FIGURE 22. STORED CHARGE vs RATE OF CHANGE OF CURRENT

Typical Performance Curves Unless Otherwise Specified (Continued)

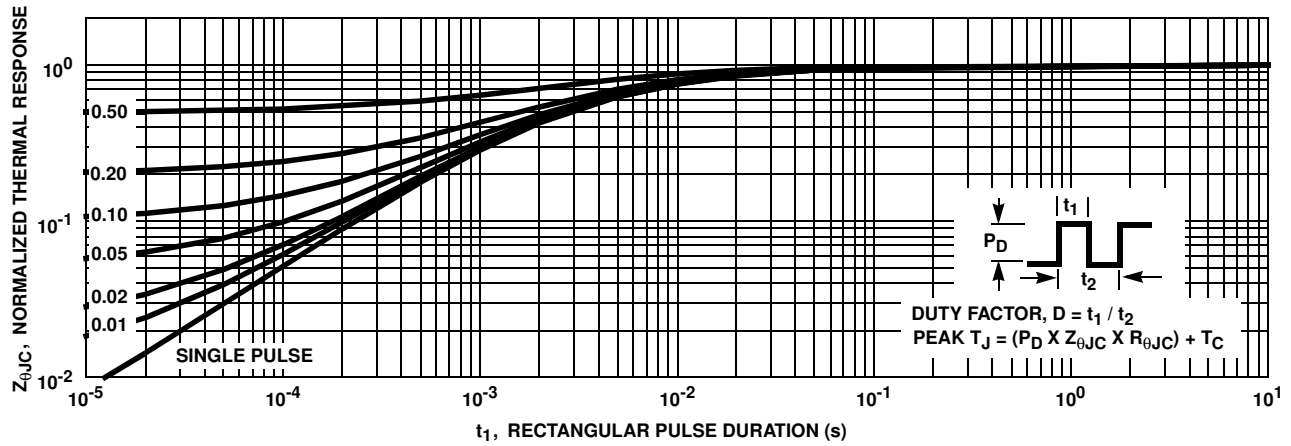


FIGURE 23. IGBT NORMALIZED TRANSIENT THERMAL RESPONSE, JUNCTION TO CASE

Test Circuit and Waveforms

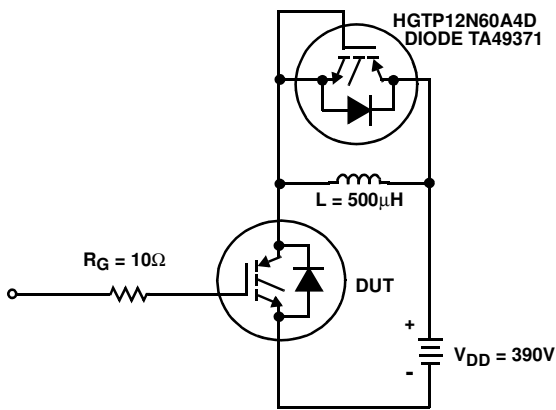


FIGURE 24. INDUCTIVE SWITCHING TEST CIRCUIT

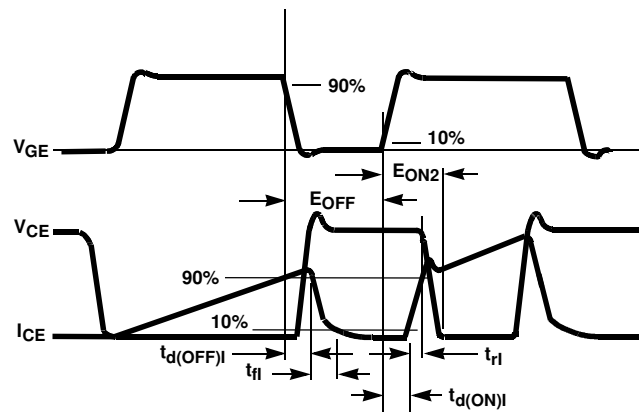


FIGURE 25. SWITCHING TEST WAVEFORMS



## Handling Precautions for IGBTs

Insulated Gate Bipolar Transistors are susceptible to gate-insulation damage by the electrostatic discharge of energy through the devices. When handling these devices, care should be exercised to assure that the static charge built in the handler's body capacitance is not discharged through the device. With proper handling and application procedures, however, IGBTs are currently being extensively used in production by numerous equipment manufacturers in military, industrial and consumer applications, with virtually no damage problems due to electrostatic discharge. IGBTs can be handled safely if the following basic precautions are taken:

1. Prior to assembly into a circuit, all leads should be kept shorted together either by the use of metal shorting springs or by the insertion into conductive material such as "ECCOSORB™ LD26" or equivalent.
2. When devices are removed by hand from their carriers, the hand being used should be grounded by any suitable means - for example, with a metallic wristband.
3. Tips of soldering irons should be grounded.
4. Devices should never be inserted into or removed from circuits with power on.
5. **Gate Voltage Rating** - Never exceed the gate-voltage rating of  $V_{GEM}$ . Exceeding the rated  $V_{GE}$  can result in permanent damage to the oxide layer in the gate region.
6. **Gate Termination** - The gates of these devices are essentially capacitors. Circuits that leave the gate open-circuited or floating should be avoided. These conditions can result in turn-on of the device due to voltage buildup on the input capacitor due to leakage currents or pickup.
7. **Gate Protection** - These devices do not have an internal monolithic Zener diode from gate to emitter. If gate protection is required an external Zener is recommended.


## Operating Frequency Information

Operating frequency information for a typical device (Figure 3) is presented as a guide for estimating device performance for a specific application. Other typical frequency vs collector current ( $I_{CE}$ ) plots are possible using the information shown for a typical unit in Figures 5, 6, 7, 8, 9 and 11. The operating frequency plot (Figure 3) of a typical device shows  $f_{MAX1}$  or  $f_{MAX2}$ ; whichever is smaller at each point. The information is based on measurements of a typical device and is bounded by the maximum rated junction temperature.

$f_{MAX1}$  is defined by  $f_{MAX1} = 0.05 / (t_{d(OFF)I} + t_{d(ON)I})$ . Deadtime (the denominator) has been arbitrarily held to 10% of the on-state time for a 50% duty factor. Other definitions are possible.  $t_{d(OFF)I}$  and  $t_{d(ON)I}$  are defined in Figure 25. Device turn-off delay can establish an additional frequency limiting condition for an application other than  $T_{JM}$ .  $t_{d(OFF)I}$  is important when controlling output ripple under a lightly loaded condition.

$f_{MAX2}$  is defined by  $f_{MAX2} = (P_D - P_C) / (E_{OFF} + E_{ON2})$ . The allowable dissipation ( $P_D$ ) is defined by  $P_D = (T_{JM} - T_C) / R_{\theta JC}$ . The sum of device switching and conduction losses must not exceed  $P_D$ . A 50% duty factor was used (Figure 3) and the conduction losses ( $P_C$ ) are approximated by  $P_C = (V_{CE} \times I_{CE}) / 2$ .

$E_{ON2}$  and  $E_{OFF}$  are defined in the switching waveforms shown in Figure 25.  $E_{ON2}$  is the integral of the instantaneous power loss ( $I_{CE} \times V_{CE}$ ) during turn-on and  $E_{OFF}$  is the integral of the instantaneous power loss ( $I_{CE} \times V_{CE}$ ) during turn-off. All tail losses are included in the calculation for  $E_{OFF}$ ; i.e., the collector current equals zero ( $I_{CE} = 0$ ).

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## PUBLICATION ORDERING INFORMATION

### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor  
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA  
**Phone:** 303-675-2175 or 800-344-3860 Toll Free USA/Canada  
**Fax:** 303-675-2176 or 800-344-3867 Toll Free USA/Canada  
**Email:** [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

**N. American Technical Support:** 800-282-9855 Toll Free  
USA/Canada  
**Europe, Middle East and Africa Technical Support:**  
Phone: 421 33 790 2910  
**Japan Customer Focus Center**  
Phone: 81-3-5817-1050

**ON Semiconductor Website:** [www.onsemi.com](http://www.onsemi.com)  
**Order Literature:** <http://www.onsemi.com/orderlit>  
For additional information, please contact your local  
Sales Representative